ABSTRACT OF THE DISCLOSURE

A semiconductor chip having a plurality of device formative layers that are formed into an integrated thin film is provided by a technique for transferring. According to the present invention, a semiconductor chip that is formed into a thin film and that is highly integrated can be manufactured by transferring a device formative layer with a thickness of at most 50μm which is separated from a substrate into another substrate by a technique for transferring, and transferring another device formative layer with a thickness of at most 50μm which is separated from another substrate to the above device formative layer, and, repeating such transferring process.